Unit in mm

TOSHIBA PHOTOCOUPLER GaAlAs IRED + PHOTO-IC

TLP719

Digital logic ground isolation

Line receivers

Microprocessor system interfaces

Switching power supply feedback control

Transistor invertors

The TOSHIBA TLP719 consists of a GaAlAs high-output light-emitting diode and a high-speed detector.

This unit is a 6-lead SDIP. The TLP719 is 50% smaller than the 8-pin DIP and meets the reinforced insulation class requirements of international safety standards. Therefore the mounting area can be reduced in equipment requiring safety standard certification.

The TLP719 has a Faraday shield integrated on the photodetector chip to provide an effective common mode noise transient immunity. Therefore this product is suitable for application in noisy environmental conditions.

· Open collector

Package type : SDIP6

• Isolation voltage : 5000 Vrms (min)

Common mode transient immunity : ±10 kV/us(min) @V_{CM} = 400 V

• Switching speed : $t_{pHL}/t_{pLH} = 0.8 \mu s \text{ (max)}$

@ I_F = 16 mA , V_{CC} = 5 V, R_L = 1.9 k Ω , Ta = 25 °C

TTL compatible

Construction mechanical rating

	7.62-mm pitch standard type	10.16-mm pitch TLPXXXF type
Creepage Distance	7.0 mm (min)	8.0 mm (min)
Clearance	7.0 mm (min)	8.0 mm (min)
Insulation Thickness	0.4 mm (min)	0.4 mm (min)

UL recognized : UL1577, File No. E67349

• Option (D4)

TÜV approved : EN60747-5-2

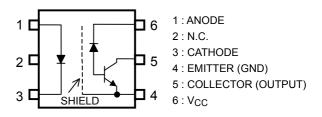
Certificate No. R50033433

Maximum operating insulation voltage: 890 Vpk Highest permissible over voltage: 8000 Vpk

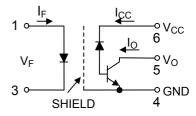
(Note) When a EN60747-5-2 approved type is needed, please designate the "Option(D4)"

4.58±0.25 6 5 4 9 9 7.62±0.25 1 2 3 9.70 1.27±0.2 1.25±0.25 0.4±0.1 9.7±0.3 TOSHIBA 11-5J1 Weight: 0.26 g (typ.)

PIN CONFIGURATION (Top View)



SCHEMATIC



A 0.1- μ F bypass capacitor must be connected between pins 4 and 6. (See Note 7.)

Maximum Ratings (Ta = 25 °C)

	Characteristic		Symbol	Rating	Unit
	Forward current	(Note 1)	ΙF	25	mA
	Pulse forward current	(Note 2)	IFP	50	mA
LED	Peak transient forward current	(Note 3)	I _{FPT}	1	Α
H	Reverse voltage		V _R	5	٧
	Diode power dissipation	(Note 4)	P_{D}	45	mW
	Junction temperature		Tj	125	°C
	Output current		IO	8	mA
	Peak output current		IOP	16	mA
Detector	Output voltage		Vo	-0.5~20	٧
Dete	Supply voltage		V _{CC}	-0.5~30	٧
	Output power dissipation	(Note 5)	PO	100	mW
	Junction Temperature		Tj	125	°C
Оре	rating temperature range		T _{opr}	-55~100	°C
Stor	Storage temperature range		T _{stg}	-55~125	°C
Lea	d soldering temperature (10 s)		T _{sol}	260	°C
Isola	ation voltage (AC, 1 minute, R.H.≤ 60 %)	(Note 6)	BVS	5000	Vrms

Note 1 : Derate 0.45 mA / °C above 70 °C.

Note 2 : 50% duty cycle, 1 ms pulse width. Derate 0.9 mA / °C above 70 °C.

Note 3 : Pulse width \leq 1 μ s, 300 pps.

Note 4: Derate 0.8 mW / °C above 70 °C.

Note 5 : Derate 1.8 mW / °C above 70 °C.

Note 6: Device considered a two-terminal device: pins 1, 2 and 3 paired with pins 4, 5 and 6 respectively.

Note 7 : A ceramic capacitor $(0.1~\mu\text{F})$ should be connected from pin 6 to pin 4 to stabilize the operation of the high-gain linear amplifier. Failure to provide the bypassing may impair the switching property. The total lead length between capacitor and coupler should not exceed 1 cm.

Electrical Characteristics (Ta = 25 °C)

Characteristic		Symbol	Test Condition	Min.	Тур.	Max.	Unit
	Forward voltage	V _F	I _F = 16 mA		1.65	1.85	V
ED	Forward voltage Temperature coefficient	ΔV _F / ΔTa	I _F = 16 mA	_	-2	_	mV / °C
=	Reverse current	I _R	V _R = 5 V	_	_	10	μΑ
	Capacitance between terminals	C _T	V _F = 0 V , f = 1 MHz	_	45	_	pF
Detector	HIGH-level output current	I _{OH} (1)	$I_F = 0 \text{ mA}, V_{CC} = V_O = 5.5 \text{ V}$	_	3	500	nA
		I _{OH} (2)	$I_F = 0 \text{ mA}, V_{CC} = 30 \text{ V}$ $V_O = 20 \text{ V}$	_	_	5	
		Іон	$I_F = 0 \text{ mA }, V_{CC} = 30 \text{ V}$ $V_O = 20 \text{ V}, Ta = 70 ^{\circ}\text{C}$	_	_	50	μΑ
۵	HIGH-level supply current	Іссн	I _F = 0 mA ,V _{CC} = 30 V	_	0.01	1	μΑ
	Supply voltage	V _{CC}	I _{CC} = 0.01 mA	30	_	_	V
	Output voltage	VO	I _O = 0.5 mA	20	_		V

Coupled Electrical Characteristics (Ta = 25 °C)

Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Current transfer ratio	I _O / I _F	$I_F = 16 \text{ mA}, V_{CC} = 4.5 \text{ V}$ $V_O = 0.4 \text{ V}$	20	_	_	%
LOW-level output voltage	V _{OL}	$I_F = 16 \text{ mA}, V_{CC} = 4.5 \text{ V}$ $I_O = 2.4 \text{ mA}$	ı	ı	0.4	V

Isolation Characteristics (Ta = 25 °C)

Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Capacitance input to output	CS	V = 0 V , f = 1 MHz (Note 6)	_	8.0	_	pF
Isolation resistance	R _S	R.H. ≤ 60% ,V _S = 500 V (Note 6)	1×10 ¹²	10 ¹⁴	_	Ω
Isolation voltage	BVS	AC, 1 minute	5000	_	_	V
		AC, 1 second , in oil	_	10000	-	V _{rms}
		DC, 1 minute , in oil	_	10000	-	Vdc

Switching Characteristics (Ta = 25 °C, V_{CC} = 5 V)

Characteristic	Symbol	Test Cir- cuit	Test Condition	Min.	Тур.	Max.	Unit
Propagation delay time $(H \rightarrow L)$	t _{pHL}	- Fig1	$I_F = 0 \rightarrow 16 \text{ mA}$ $R_L = 1.9 \text{k}\Omega$	_	_	0.8	μs
Propagation delay time $(L \rightarrow H)$	t _{pLH}		$I_F = 16 \rightarrow 0 \text{ mA}$ $R_L = 1.9 \text{k}\Omega$	_	_	0.8	μs
Common mode transient immunity at logic HIGH output (Note 8)	CM _H	- Fig2	$I_F = 0 \text{ mA}$ $V_{CM} = 400 \text{ Vp-p}$ $R_L = 1.9 \text{k}\Omega$	10000	-		V / µs
Common mode transient immunity at logic LOW output (Note 8)	CML		$I_F = 16 \text{ mA}$ $V_{CM} = 400 \text{ Vp-p}$ $R_L = 1.9 \text{ k}\Omega$	-10000	_	_	V / µs

Note 8 : CM_L is the maximum rate of fall of the common mode voltage that can be sustained with the output voltage in the logic LOW state ($V_O < 0.8 \text{ V}$).

 CM_H is the maximum rate of rise of the common mode voltage that can be sustained with the output voltage in the logic HIGH state ($V_O > 2 V$).

Figure 1. Switching Time Test Circuit

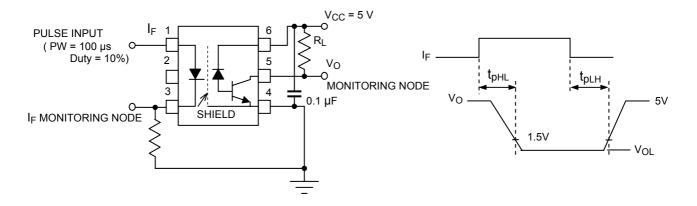
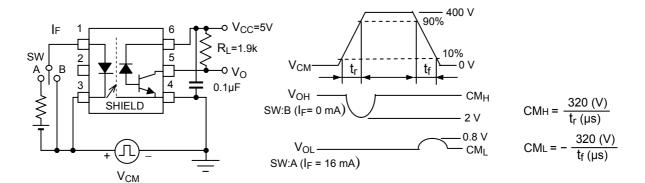
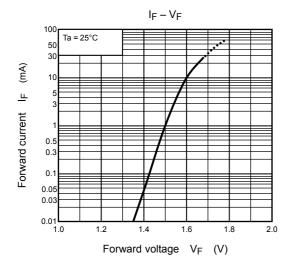
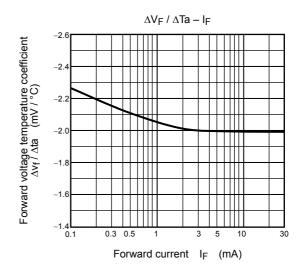
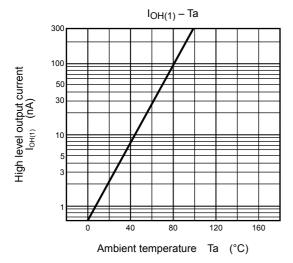


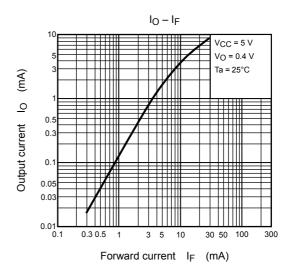
Figure 2. Common Mode Noise Immunity Test Circuit.

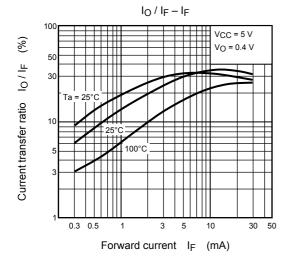


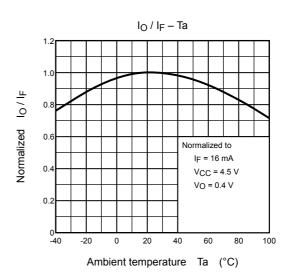


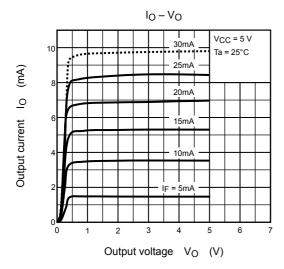


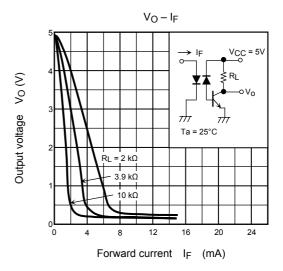


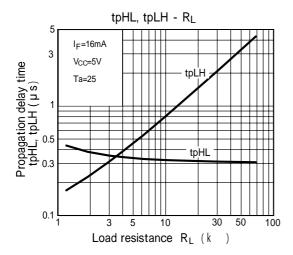


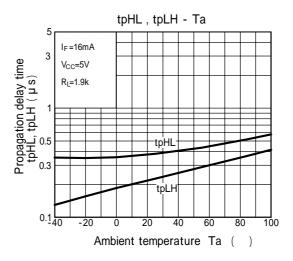












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